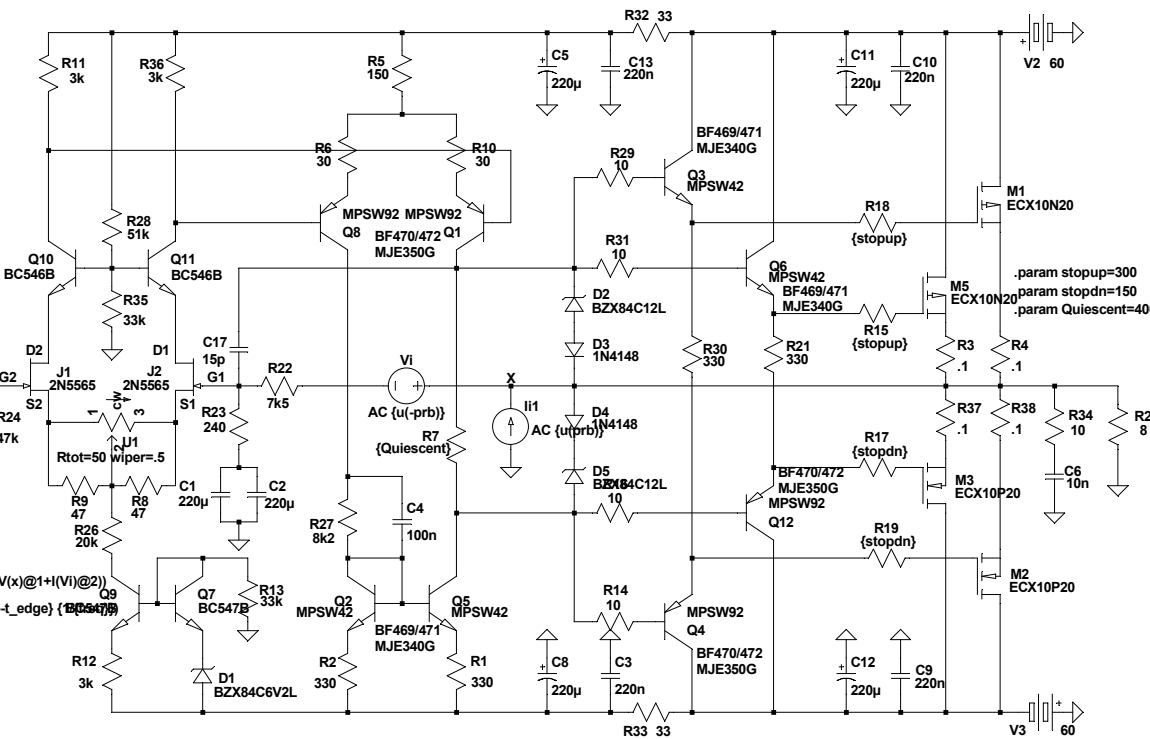


.MODEL 2N5565 NJF(VTO=-1.447 BETA=9.109m BETATCE=-0.5 LAMBDA=7.5m RD=1 RS=1 CGS=9.76p CGD=8.67p PB=1 IS=94.42f XTI=3 AF=1 FC=0.5 N=1 NR=2 MFG=NSC)



```
.SUBCKT ECX10N20 1 2 3
M1 9 7 8 8 MM L=1 W=1
* Default values used in MM:
* The capacitances are added externally
* Other default values are:
* RS=0 RD=0 LD=0 CBD=0 CBS=0 CGBO=0
.MODEL MM NMOS LEVEL=1 IS=1e-32
+VTO=0.473 LAMBDA=0.092 KP=1.585
RS 8 3 0.41
D1 8 9 MD
.MODEL MD D IS=1.0e-32 N=50 BV=250
+CJO=1.0e-9 VJ=0.7 M=0.5
RDS 8 9 1e+06
RD 9 1 0.58
RG 2 7 80
* Gate Source capacitance Cgs0
CAP1 7 8 400e-12
*****
* Gate Drain capacitance Cdg0
CAP 7 4 10.5e-12
*****
* Gate Drain Capacitance Cdgj0
* Modelled as a diode
D2 4 9 MDD
.MODEL MDD D IS=1e-32 N=50
+CJO=94.8e-12 VJ=0.3 M=1
*****
.ENDS ECX10N20

.SUBCKT ECX10P20 1 2 3
M1 9 7 8 8 MM L=1 W=1
* Default values used in MM:
* The capacitances are added externally
* Other default values are:
* RS=0 RD=0 LD=0 CBD=0 CBS=0 CGBO=0
.MODEL MM PMOS LEVEL=1 IS=1e-32
+VTO=-0.426 LAMBDA=0.073 KP=0.673
RS 8 3 0.342
D1 9 8 MD
.MODEL MD D IS=1.0e-32 N=50 BV=250
+CJO=1.45e-9 VJ=0.446 M=0.377
RDS 8 9 1e+06
RD 9 1 0.523
RG 2 7 45.2
* Gate Source capacitance Cgs0
CAP1 7 8 696e-12
*****
* Gate Drain capacitance Cdg0
CAP 7 4 15.2e-12
*****
* Gate Drain Capacitance Cdgj0
* Modelled as a diode
D2 9 4 MDD
.MODEL MDD D IS=1e-32 N=50
+CJO=27.6e-12 VJ=0.817 M=0.871
*****
.ENDS ECX10P20
```

.inc potentiometer.sub